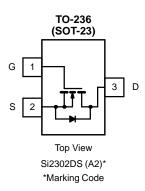


N-Channel 1.25-W, 2.5-V MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)	
20	0.085 @ V _{GS} = 4.5 V	2.8	
	0.115 @ V _{GS} = 2.5 V	2.4	



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20	V		
Gate-Source Voltage		V _{GS}	±8			
Continuous Drain Current (T.j = 150°C)b	T _A = 25°C		2.8			
Continuous Diam Current (1) = 150 C)	T _A = 70°C	'D	2.2			
Pulsed Drain Current ^a		I _{DM}	10	^		
Continuous Source Current (Diode Conduction) ^b		I _S	1.6			
Power Dissipation ^b	T _A = 25°C	В	1.25	w		
rowei Dissipation-	T _A = 70°C	P _D	0.80	— **		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient ^b	В	100	°C/W	
Maximum Junction-to-Ambient ^c	R _{thJA}	166	C/VV	

Notes

- Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board, $t \le 5$ sec.
- Surface Mounted on FR4 Board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

Vishay Siliconix



SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static			•	•				
Drain-Source Breakdown Voltage	V(_{BR)DSS}	$V_{GS} = 0 \text{ V, I}_{D} = 10 \mu\text{A}$	20					
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 50 \mu A$	0.65			-		
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	T		
	DSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	μΑ		
On-State Drain Current ^a	1	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	6					
	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 2.5 \text{ V}$	4			A		
Drain-Source On-Resistance ^a	_	$V_{GS} = 4.5 \text{ V}, I_D = 3.6 \text{ A}$		0.07	0.085	Ω		
	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 3.1 \text{ A}$		0.085	0.115			
Forward Transconductance ^a	9fs	$V_{DS} = 5 \ V, I_D = 3.6 A$		10		S		
Diode Forward Voltage	V _{SD}	$I_S = 1.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.76	1.2	V		
Dynamic	-							
Total Gate Charge	Qg			5.4	10	nC		
Gate-Source Charge	Q_{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 3.6 A		0.65				
Gate-Drain Charge	Q_{gd}			1.60				
Input Capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		340				
Output Capacitance	C _{oss}			115		pF		
Reverse Transfer Capacitance	C _{rss}			33				
Switching	-		-					
Turn-On Delay Time	t _{d(on)}	$V_{DD} = 10 \text{ V}, R_L = 5.5 \Omega$ $I_D \cong 3.6 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_G = 6 \Omega$		12	25	ns		
Rise Time	t _r			36	60			
Turn-Off Delay Time	t _{d(off)}			34	60			
Fall-Time	t _f			10	25			

VNLR02

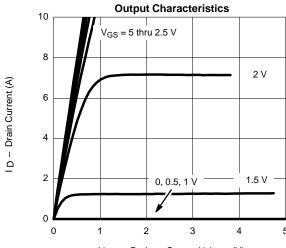
Notes a. Pulse test: PW \leq 300 μ s duty cycle \leq 2%..

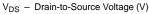


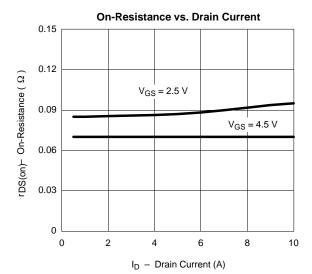




TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)







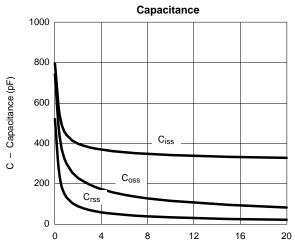
 $I_D = 3.6 \text{ A}$ VGS - Gate-to-Source Voltage (V) 3 2 0 0 1 2 5 6

Q_g - Total Gate Charge (nC)

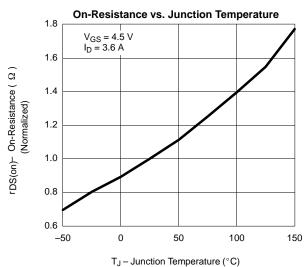
Gate Charge

Transfer Characteristics 10 8 - Drain Current (A) 6 T_C = 125°C 4 \Box 2 25°C –55°C 0 0 0.5 1.0 2.0 2.5

V_{GS} - Gate-to-Source Voltage (V)



V_{DS} - Drain-to-Source Voltage (V)



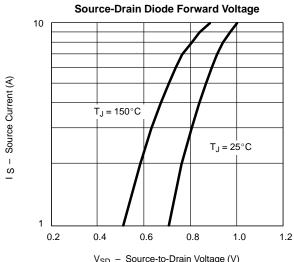
5

 $V_{DS} = 10 \text{ V}$

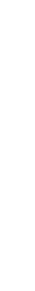
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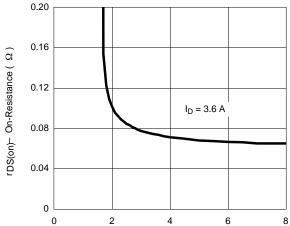
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



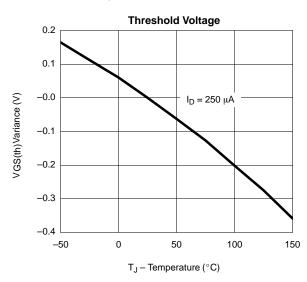


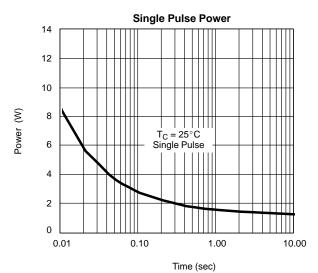


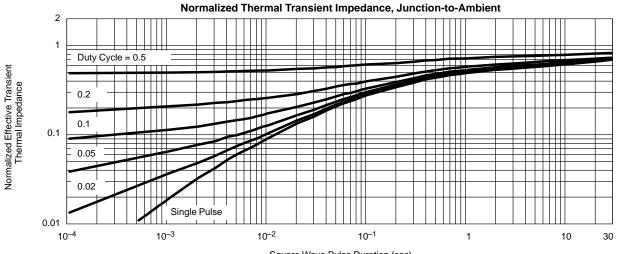
On-Resistance vs. Gate-to-Source Voltage



V_{GS} - Gate-to-Source Voltage (V)









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Document Number: 91000 Revision: 18-Jul-08